Invited talks at conferences

1. "Electronic and crystal structure in pseudopotential theory",
P. Boguslawski,

2. "Crystallographic and electronic properties of GaAs/InAs monolayer superlattice",
A. Baldereschi and P. Boguslawski,

3. "Microscopic crystallographic properties of semiconductor alloys",
A. Baldereschi and P. Boguslawski,

4. "Atomic-scale structure of semiconductor alloys",
P. Boguslawski,

5. "Surface stability of lattice-mismatched semiconductor alloys",
P. Boguslawski,
CECAM Workshop on physics of semiconductor interfaces, Paris 1990.

6. "Atomic-scale morphology of semiconductor heterointerfaces",
P. Boguslawski,

7. "Surface energetics and epitaxial growth of Si/Ge systems",
P. Boguslawski,

8. "Microscopic structure of Si(001) with monoatomic steps",
P. Boguslawski, Q.M. Zhang, Z. Zhang, and J. Bernholc,

J. Bernholc, P. Boguslawski, E. Briggs, T. A. White,

10. "Ab initio and classical MD simulations of diffusion and growth",
J. Bernholc, P. Boguslawski, C. J. Brabec, B. Chen, A. Maiti, C. Roland, Q. Zhang, and Z. Zhang,

11. "Mesoscopy and Microscopy of Silicon Surfaces",
P. Boguslawski,
22th Int. School on Semiconductors, Jaszowiec 1994.

12. "Calculated Properties of native defects in GaN",
P. Boguslawski, E. Briggs, and J. Bernholc,


24. "Ab Initio Simulations of the Si (100) Surface: Step Flow and Melting" C. Roland, M. Wensell, Q.M. Zhang, P. Boguslawski and J. Bernholc,
25. "Donors, Defects, and Surface Segregation in AlGaN Alloys",
P. Bogusławski, K. Rapcewicz, E. L. Briggs, and J. Bernholc,
March Meeting of the American Physical Society, Los Angeles, 16-20 March 1998.

26. "Ab-initio studies of SiGe(001) surfaces",
P. Bogusławski and J. Bernholc,

K. Rapcewicz, P. Bogusławski, E. L. Briggs, C. Bungaro, M. Buongiorno Nardelli and J. Bernholc,
Workshop on Surface Morphology, Interfaces, and Growth of the III-Nitrides, Ringberg Castle, Germany, January 1998.

P. Bogusławski and J. Bernholc,

29. "Surface effects in impurity incorporation, alloying and the formation of inversion domains",
K. Rapcewicz, P. Bogusławski, C. Bungaro, J. Bernholc,
March Meeting of the American Physical Society, Atlanta, March 1999.

30. "Polarization and strain effects at interfaces",
J. Bernholc, P. Bogusławski, M. Buongiorno Nardelli, and K. Rapcewicz

31. "Epitaxy of semiconductor heterostructures: surface processes in the atomic scale",
P. Bogusławski,

32. "Doping issues in III-nitrides"
P. Bogusławski and J. Bernholc,

33. "Theory of Mn-induced magnetization in GaMnAs"
P Boguslawski

34. "Theory of magnetic properties of Mn in (Ga,Mn)N"
P. Bogusławski,
German-Polish workshop on Physics and Semiconductors of Nitride Semiconductors, Germany, Berlin, February 2004

35. "Growth of p-type ZnO by Oxidation of Zn-based Compounds"
E. Kaminska, E. Przedziecka, A. Piotrowska, I. Pasternak, P. Boguslawski, J. Kossut, E. Dynowska, and R. Jakiela,
36. "Theory of interfacial interdiffusion and electromigration of H, dopants, and vacancies in GaN/AlN"
P. Boguslawski, J. Bernholc, N. Gonzalez Szwacki, P. Jakubas

37. "Magnetism based on p-orbitals",
P. Bogusławski, O. Volnianska,
18th Int. Materials Research Congress 2009, Cancun, Mexico 2009

38. "Dopants and defects in semiconductors"
P. Bogusławski
39th Int. Conference on Semiconductors Jaszowiec 2010.